

**N-Ch MOSFET** 

#### **General Description**

The WSK180N03 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK180N03 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

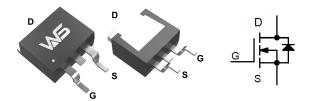
## **Product Summery**

BVDSS	RDSON	ID
30V	2.0mΩ	180A

#### Applications

- High Frequency Point-of-Load Synchronous
  Buck Converter
- Networking DC-DC Power System

# **TO-263-2L Pin Configuration**



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage 30		V
V <sub>GS</sub>	Gate-Source Voltage ±20		V
I₀@T₀=25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 180		A
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 145		A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	500	А
EAS	Single Pulse Avalanche Energy <sup>3</sup>	246	mJ
I <sub>AS</sub>	Avalanche Current	70.2	A
P₀@T₀=25℃	Total Power Dissipation <sup>3</sup>	187	W
P₀@T₀=100℃	Total Power Dissipation <sup>3</sup>	90	W
T <sub>STG</sub>	Storage Temperature Range -55 to 175		°C
TJ	Operating Junction Temperature Range	-55 to 175	°C



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## Electrical Characteristics (T<sub>J</sub>=25 <sup>•</sup>C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$ , I_D=1mA		0.014		V/℃
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A		2.0	2.8	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		2.6	3.5	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage		1.2		2.5	V
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient			-4.0		mV/℃
I <sub>DSS</sub>	Drain Source Lookage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA
	Drain-Source Leakage Current	$V_{DS}$ =24V , $V_{GS}$ =0V , $T_{J}$ =55 $^{\circ}\mathrm{C}$			5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm20V$ , $V_{DS}$ = $0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =30A		50		S
Qg	Total Gate Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =15A		57		
Q <sub>gs</sub>	Gate-Source Charge			14		nC
Q <sub>gd</sub>	Gate-Drain Charge			24		
T <sub>d(on)</sub>	Turn-On Delay Time			21		
Tr	Rise Time			6.3		- ns
T <sub>d(off)</sub>	Turn-Off Delay Time			124.6		
T <sub>f</sub>	Fall Time			15.8		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		5851		
C <sub>oss</sub>	Output Capacitance			720		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			525		

## **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	$V_G = V_D = 0V$ , Force Current			205	А
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>				500	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25℃			1.2	V

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width  $\,\leq\,$  300us , duty cycle  $\,\leq\,$  2%

3. The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =70.2A

4.The power dissipation is limited by 175°C junction temperature

5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

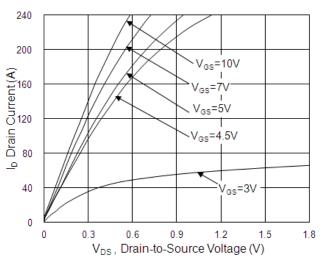
6.Package limitation current is 120A.



WSK180N03

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# **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

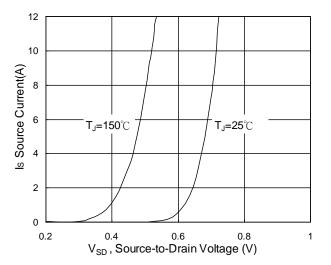
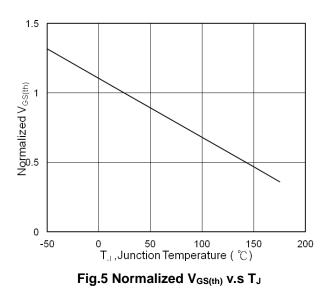


Fig.3 Forward Characteristics of Reverse



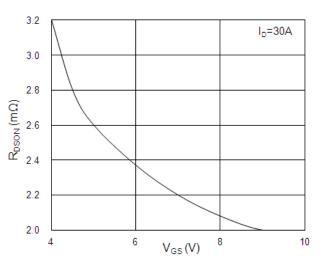
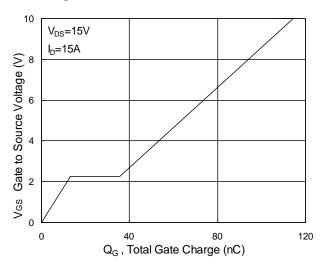
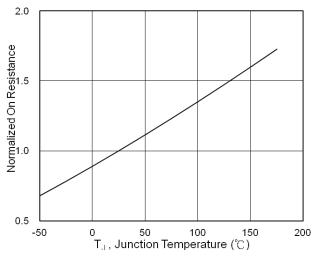


Fig.2 On-Resistance v.s Gate-Source



**Fig.4 Gate-Charge Characteristics** 







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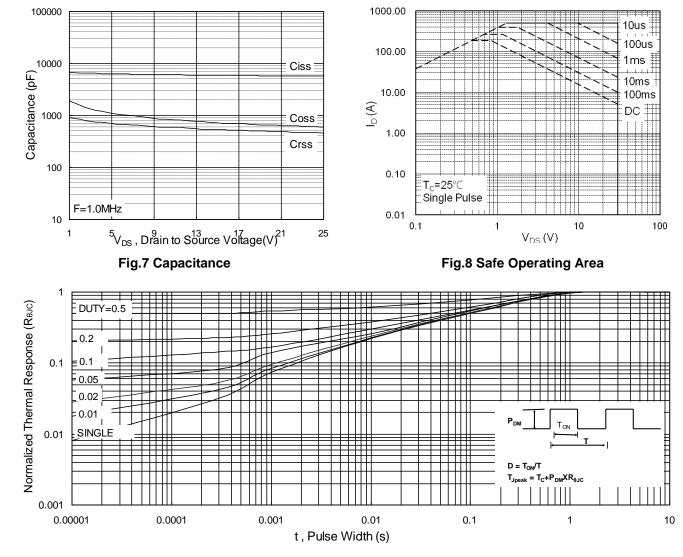


Fig.9 Normalized Maximum Transient Thermal Impedance

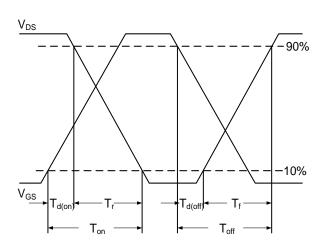


Fig.10 Switching Time Waveform

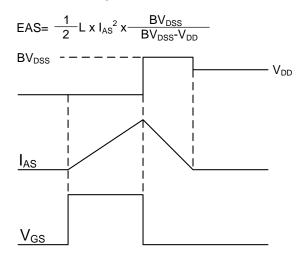


Fig.11 Unclamped Inductive Switching Waveform



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